**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS306PX

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

## 3. Applications

- High-voltage DC-to-DC conversion
- · High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	100	V
I <sub>C</sub>	collector current		-	-	4.5	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	9	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	40	56	mΩ



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector	1 1	
3	В	base	3 2 1	В — [
			SOT89	sym123

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS306NX	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

# 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PBSS306NX	%5G

[1] % = placeholder for manufacturing site code

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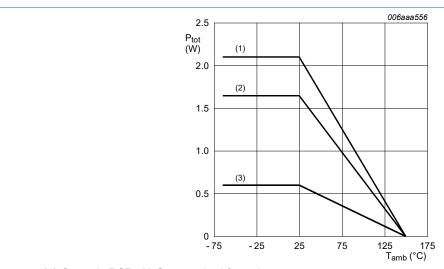
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	100	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	100	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	4.5	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	9	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint. [3]



- (1) Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm<sup>2</sup>
- (3) FR4 PCB, standard footprint

Fig. 1. **Power derating curves** 

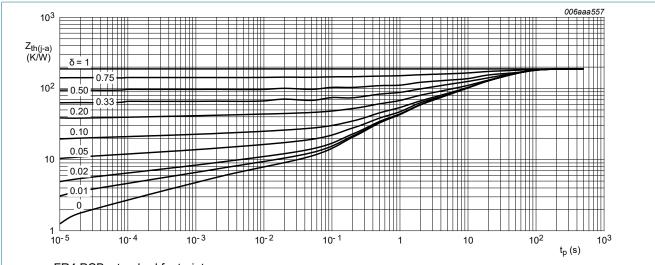
100 V, 4.5 A NPN low VCEsat transistor

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	208	K/W
junction to	junction to ambient		[2]	-	-	76	K/W
			[3]	-	-	60	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- [3] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

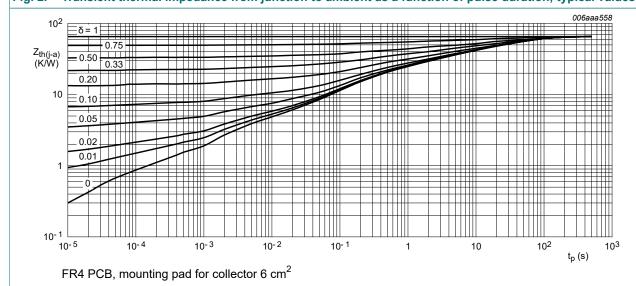
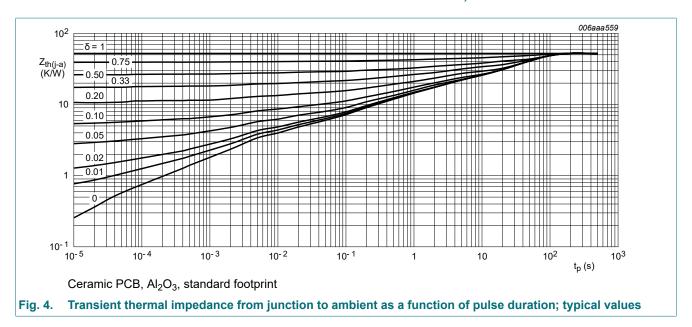


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

### 100 V, 4.5 A NPN low VCEsat transistor



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# 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 80 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	$V_{CB} = 80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 2 V; $I_{C}$ = 0.5 A; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	200	330	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 1 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	150	270	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	100	175	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 4 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	50	85	-	
		$V_{CE}$ = 2 V; $I_{C}$ = 5 A; pulsed; $t_{p}$ ≤ 300 μs; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	40	70	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = 0.5 A; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	27	40	mV
		$I_C$ = 1 A; $I_B$ = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	53	75	mV
		$I_C$ = 1 A; $I_B$ = 10 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	150	mV
		$I_C$ = 2 A; $I_B$ = 40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	115	160	mV
		$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	160	225	mV
		$I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	140	200	mV
		$I_C$ = 4.5 A; $I_B$ = 225 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; $T_{amb}$ = 25 °C	-	170	245	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 4 A; $I_B$ = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	40	56	mΩ
$V_{BEsat}$	base-emitter saturation voltage	$I_C$ = 1 A; $I_B$ = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.81	0.9	V
		$I_C$ = 4 A; $I_B$ = 400 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.94	1.05	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = 2 V; $I_{C}$ = 2 A; pulsed; $t_{p} \le 300 \ \mu s$ ; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.78	0.85	V
d	delay time	$V_{CC} = 12.5 \text{ V}; I_C = 3 \text{ A}; I_{Bon} = 0.15 \text{ A};$	-	15	-	ns
r	rise time	I <sub>Boff</sub> = -0.15 A; T <sub>amb</sub> = 25 °C	-	315	-	ns
on	turn-on time		-	330	-	ns
s	storage time		-	240	-	ns
f	fall time		-	290	-	ns
off	turn-off time		-	530	-	ns
ŤΤ	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	110	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_{E} = 0 \text{ A}; i_{e} = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	23	40	pF

### 100 V, 4.5 A NPN low VCEsat transistor

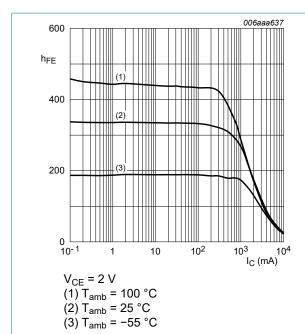


Fig. 5. DC current gain as a function of collector current; typical values

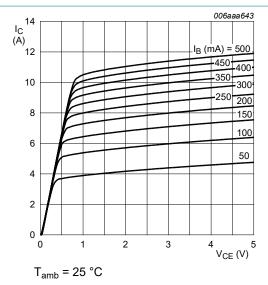


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

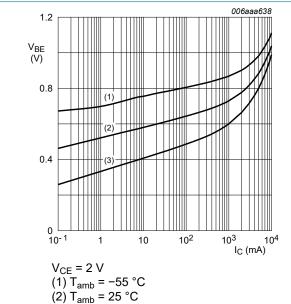
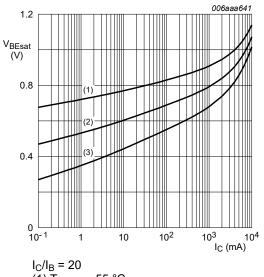


Fig. 7. Base-emitter voltage as a function of collector current; typical values

(3)  $T_{amb} = 100 \, ^{\circ}C$ 



 $I_{C}/I_{B} = 20$ (1)  $T_{amb} = -55 \,^{\circ}\text{C}$ (2)  $T_{amb} = 25 \,^{\circ}\text{C}$ (3)  $T_{amb} = 100 \,^{\circ}\text{C}$ 

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

#### 100 V, 4.5 A NPN low VCEsat transistor

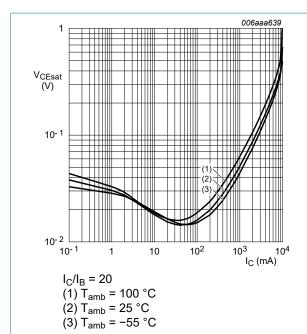


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

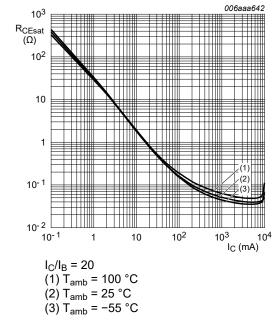


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

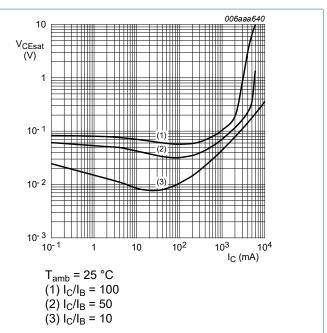


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

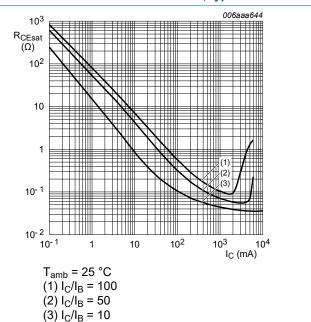
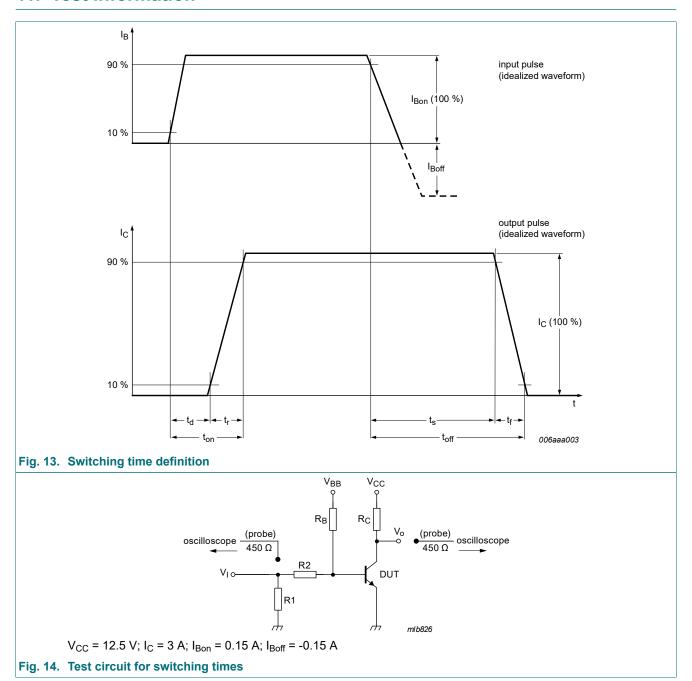


Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

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## 11. Test information

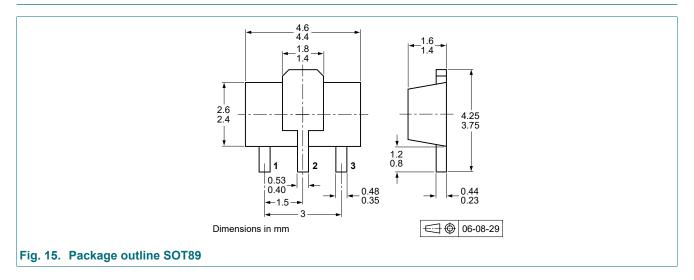


### **Quality information**

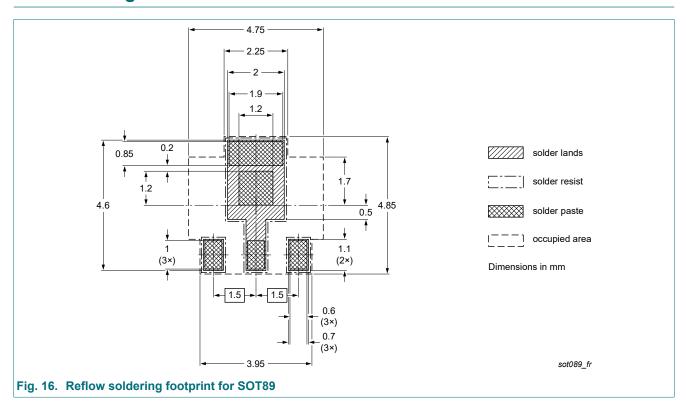
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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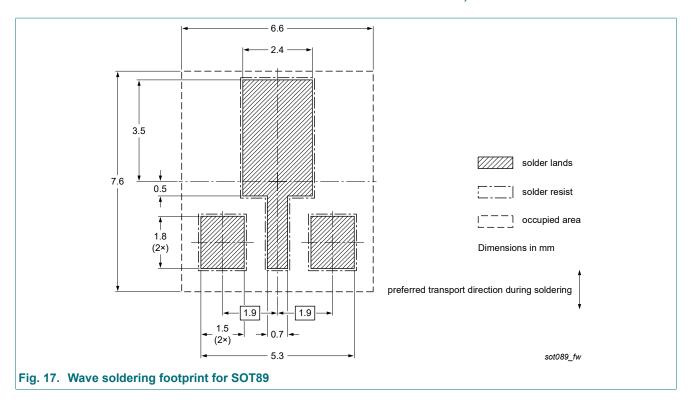
# 12. Package outline



# 13. Soldering



## 100 V, 4.5 A NPN low VCEsat transistor



### 100 V, 4.5 A NPN low VCEsat transistor

# 14. Revision history

### **Table 8. Revision history**

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS306NX v.3	20240214	Product data sheet	-	PBSS306NX_2	
Modifications:	Nexperia. • Legal texts have bee	this data sheet has been redesigned to comply with the identity guidelines of ve been adapted to the new company name where appropriate. ing information" removed.			
PBSS306NX_2	20091208	Product data sheet	-	PBSS306NX_1	
PBSS306NX_1	20060821	Product data sheet	-	-	

#### 100 V, 4.5 A NPN low VCEsat transistor

## 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the internet at <a href="https://www.nexperia.com">https://www.nexperia.com</a>.

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PBSS306N

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 14 February 2024

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